Freescale Semiconductor
Technical Data

Document Number: MRF21085-2
Rev. 11, 10/2008

RoHS

RF Power Field Effect Transistor
N-Channel Enhancement-Mode Lateral MOSFET

MRF21085LSR3

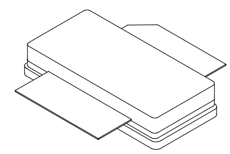
Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

- Typical 2-Carrier W-CDMA Performance: V_{DD} = 28 Volts, I_{DQ} = 1000 mA, P_{out} = 19 Watts Avg., f = 2112.5 MHz, Channel Bandwidth = 3.84 MHz, Peak/Avg. = 8.5 dB @ 0.01% Probability on CCDF.
  - Power Gain — 13.6 dB
  - Drain Efficiency — 23%
  - IM3 @ 10 MHz Offset — -37.5 dBc in 3.84 MHz Channel Bandwidth
  - ACPR @ 5 MHz Offset — -41 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 5:1 VSWR, @ 28 Vdc, 2140 MHz, 90 Watts CW Output Power

Features

- Internally Matched for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Available with Low Gold Plating Thickness on Leads. L Suffix Indicates 40μ″ Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

**2110-2170 MHz, 90 W, 28 V
LATERAL N-CHANNEL
RF POWER MOSFET**



**CASE 465A-06, STYLE 1
NI-780S**

ARCHIVE INFORMATION

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	224 1.28	W W/°C
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.78	°C/W

Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M3 (Minimum)

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Table 4. Electrical Characteristics (T_C = 25°C unless otherwise noted)

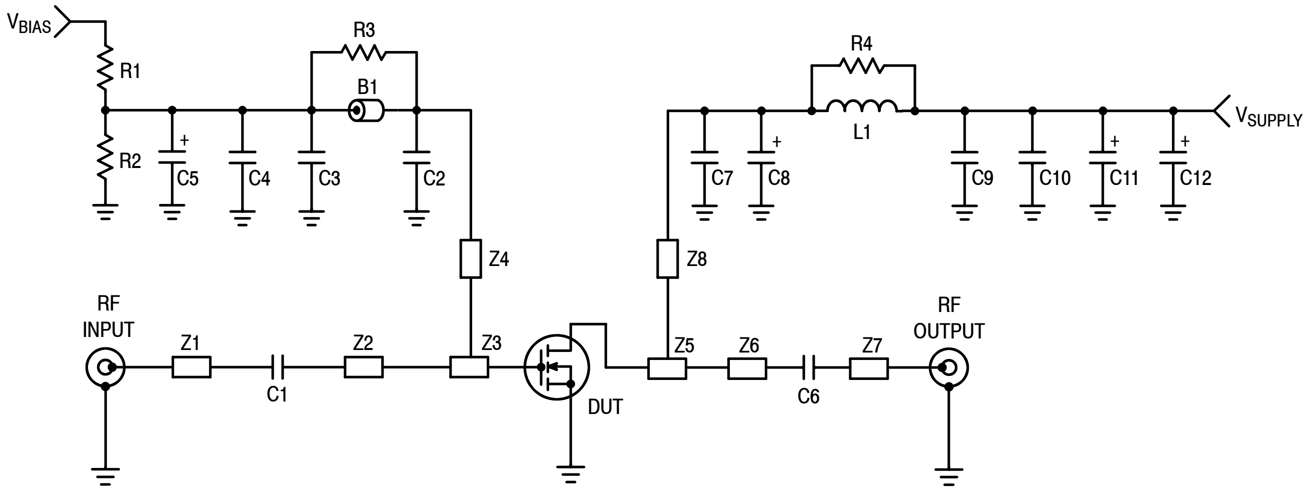
Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 100 μAdc)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 28 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	μAdc
Gate-Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	1	μAdc
On Characteristics (DC)					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 200 μAdc)	$V_{GS(th)}$	2	—	4	Vdc
Gate Quiescent Voltage (V_{DS} = 28 Vdc, I_D = 1000 mAdc)	$V_{GS(Q)}$	3	3.9	5	Vdc
Drain-Source On-Voltage (V_{GS} = 10 Vdc, I_D = 2 Adc)	$V_{DS(on)}$	—	0.18	0.21	Vdc
Dynamic Characteristics (1)					
Reverse Transfer Capacitance (V_{DS} = 28 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	3.6	—	pF
Functional Tests (In Freescale Test Fixture, 50 ohm system) 2-carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers, ACPR and IM3 measured in 3.84 MHz Bandwidth. Peak/Avg. = 8.3 dB @ 0.01% Probability on CCDF.					
Common-Source Amplifier Power Gain (V_{DD} = 28 Vdc, P_{out} = 19 W Avg., I_{DQ} = 1000 mA, f = 2112.5 MHz)	G_{ps}	12	13.6	—	dB
Drain Efficiency (V_{DD} = 28 Vdc, P_{out} = 19 W Avg., I_{DQ} = 1000 mA, f = 2112.5 MHz)	η	20	23	—	%
Third Order Intermodulation Distortion (V_{DD} = 28 Vdc, P_{out} = 19 W Avg., I_{DQ} = 1000 mA, f = 2112.5 MHz; IM3 measured over 3.84 MHz BW at f1 -10 MHz and f2 +10 MHz referenced to carrier channel power.)	IM3	—	-37.5	-35	dBc
Adjacent Channel Power Ratio (V_{DD} = 28 Vdc, P_{out} = 19 W Avg., I_{DQ} = 1000 mA, f = 2112.5 MHz; ACPR measured over 3.84 MHz at f1 -5 MHz and f2 +5 MHz.)	ACPR	—	-41	-38	dBc
Input Return Loss (V_{DD} = 28 Vdc, P_{out} = 19 W Avg., I_{DQ} = 1000 mA, f = 2112.5 MHz)	IRL	—	-12	-9	dB

1. Part is internally matched both on input and output.

(continued)

Table 4. Electrical Characteristics (T_C = 25°C unless otherwise noted) **(continued)**

Characteristic	Symbol	Min	Typ	Max	Unit
Functional Tests (In Freescale Test Fixture, 50 ohm system) **(continued)**					
Two-Tone Common-Source Amplifier Power Gain (V_{DD} = 28 Vdc, P_{out} = 90 W PEP, I_{DQ} = 1000 mA, f1 = 2110 MHz, f2 = 2120 MHz and f1 = 2160 MHz, f2 = 2170 MHz)	G_{ps}	—	13.6	—	dB
Two-Tone Drain Efficiency (V_{DD} = 28 Vdc, P_{out} = 90 W PEP, I_{DQ} = 1000 mA, f1 = 2110 MHz, f2 = 2120 MHz and f1 = 2160 MHz, f2 = 2170 MHz)	η	—	36	—	%
Two-Tone Intermodulation Distortion (V_{DD} = 28 Vdc, P_{out} = 90 W PEP, I_{DQ} = 1000 mA, f1 = 2110 MHz, f2 = 2120 MHz and f1 = 2160 MHz, f2 = 2170 MHz)	IMD	—	-31	—	dBc
Input Return Loss (V_{DD} = 28 Vdc, P_{out} = 90 W PEP, I_{DQ} = 1000 mA, f1 = 2110 MHz, f2 = 2120 MHz and f1 = 2160 MHz, f2 = 2170 MHz)	IRL	—	-12	—	dB
P_{out}, 1 dB Compression Point (V_{DD} = 28 Vdc, I_{DQ} = 1000 mA, f = 2170 MHz)	P1dB	—	100	—	W



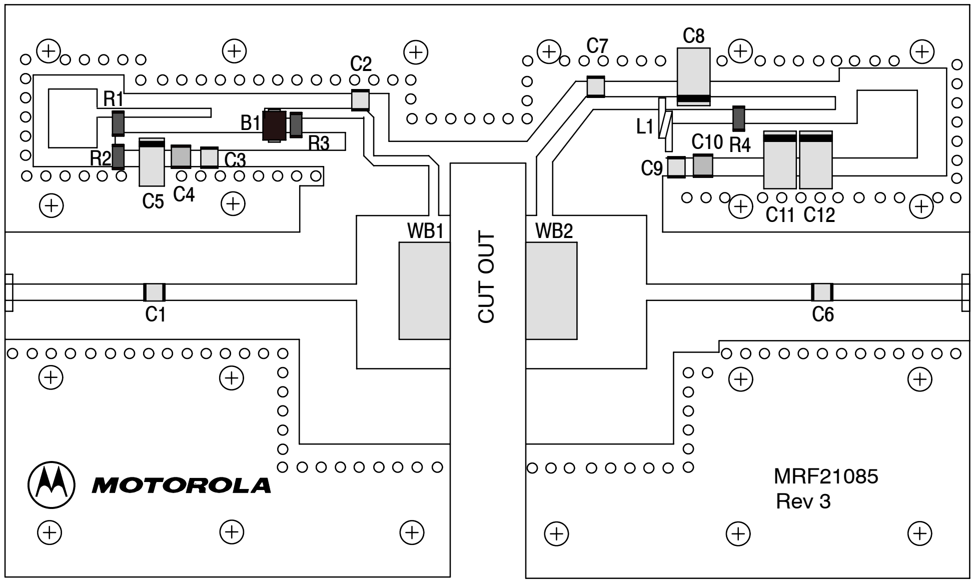
Z1	0.750″ x 0.084″ Microstrip	Board	0.030″ Glass Teflon®, Keene GX-0300-55-22, ε_r = 2.55
Z2	1.015″ x 0.084″ Microstrip		
Z3	0.480″ x 0.800″ Microstrip	PCB	Etched Circuit Boards MRF21085 Rev. 3, CMR
Z4	0.750″ x 0.050″ Microstrip		
Z5	0.610″ x 0.800″ Microstrip		
Z6	0.885″ x 0.084″ Microstrip		
Z7	0.720″ x 0.084″ Microstrip		
Z8	0.800″ x 0.070″ Microstrip		

Figure 1. MRF21085L Test Circuit Schematic

Table 5. MRF21085 Test Circuit Component Designations and Values

Designators	Description
B1	Short Ferrite Bead, Fair Rite, #2743019447
C1, C6	43 pF Chip Capacitors, ATC #100B430JCA500X
C2	10 pF Chip Capacitor, ATC #100B100JCA500X
C3, C9	1000 pF Chip Capacitors, ATC #100B102JCA500X
C4, C10	0.1 μF Chip Capacitors, Kemet #CDR33BX104AKWS
C5	1.0 μF Tantalum Chip Capacitor, Kemet #T491C105M050
C7	2.7 pF Chip Capacitor, ATC #100B2R7JCA500X
C8	10 μF Tantalum Chip Capacitor, Kemet #T495X106K035AS4394
C11, C12	22 μF Tantalum Chip Capacitors, Kemet #T491X226K035AS4394
L1	1 Turn, #20 AWG, 0.100″ ID
N1, N2	Type N Flange Mounts, Omni Spectra #3052-1648-10
R1	1.0 kΩ, 1/8 W Chip Resistor
R2	180 kΩ, 1/8 W Chip Resistor
R3, R4	10 Ω, 1/8 W Chip Resistors

ARCHIVE INFORMATION



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. MRF21085L Test Circuit Component Layout

TYPICAL CHARACTERISTICS

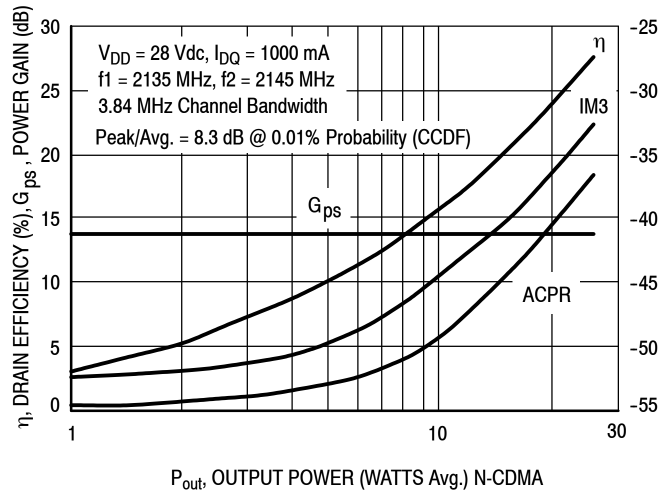


Figure 3. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

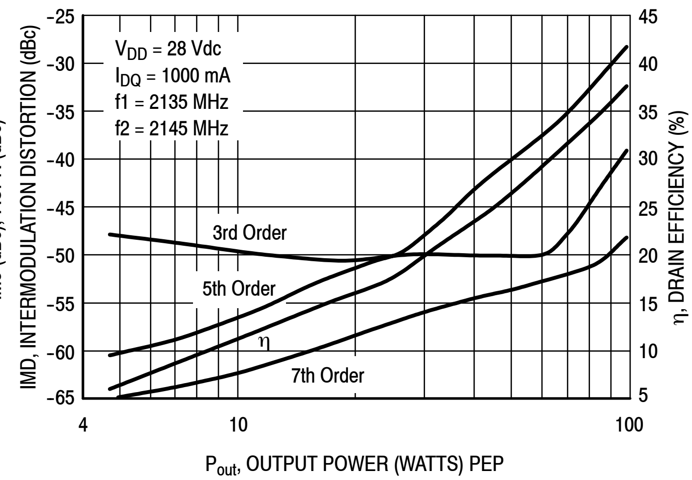


Figure 4. Intermodulation Distortion Products versus Output Power

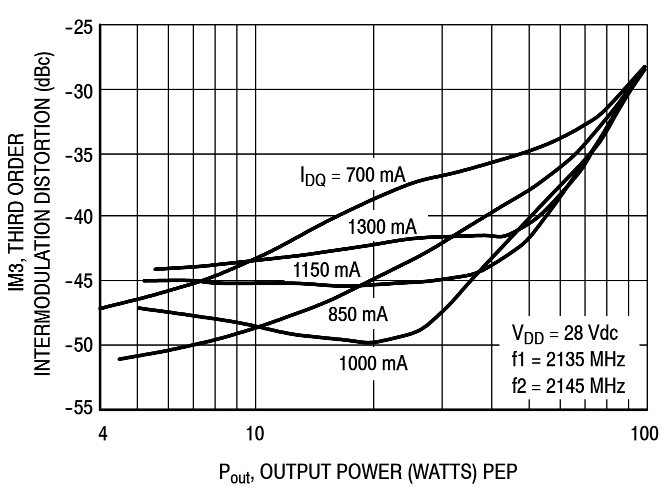


Figure 5. Third Order Intermodulation Distortion versus Output Power

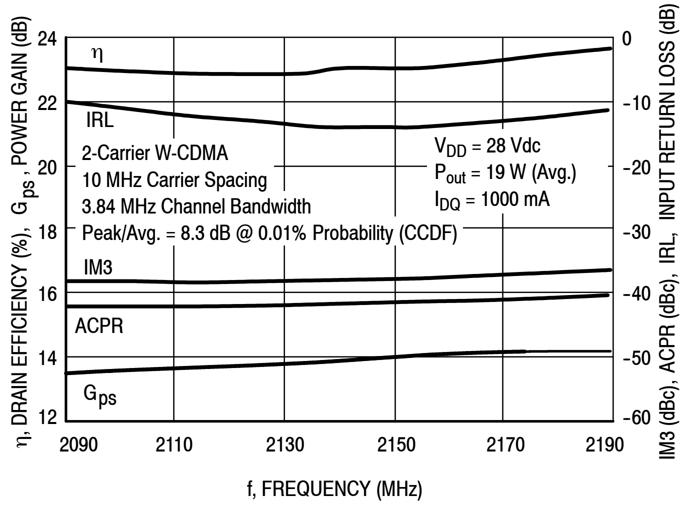


Figure 6. 2-Carrier W-CDMA Broadband Performance

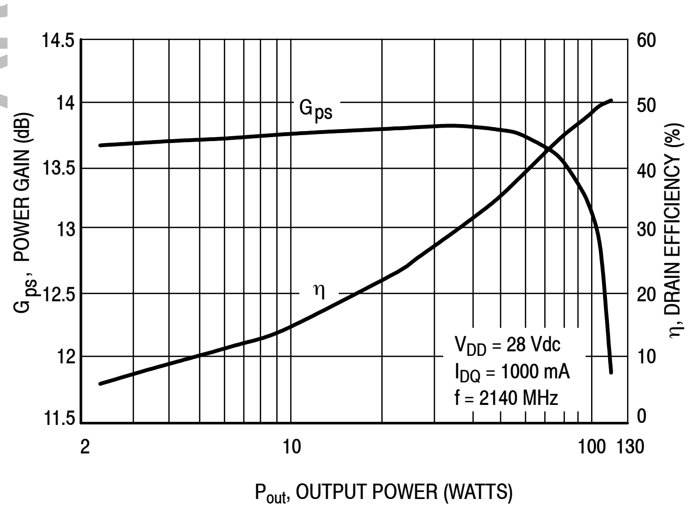


Figure 7. CW Performance

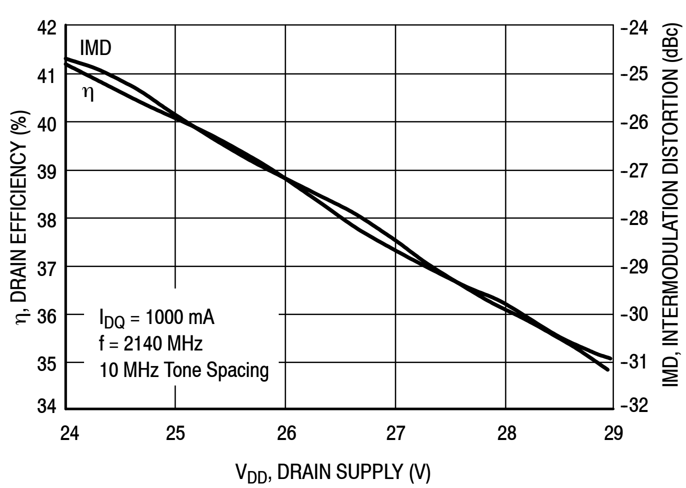


Figure 8. Two-Tone Intermodulation Distortion and Drain Efficiency versus Drain Supply

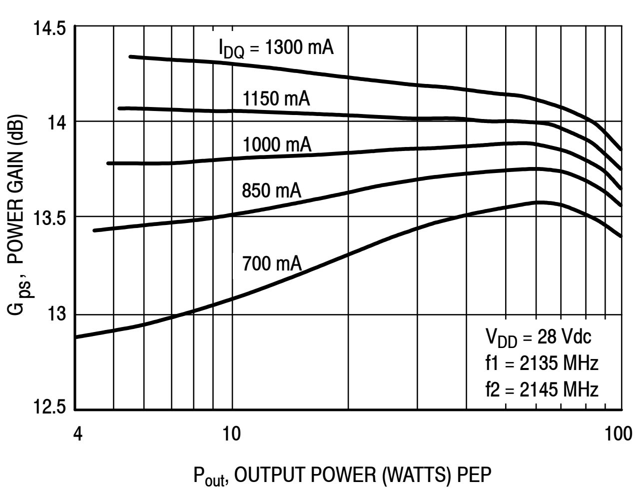


Figure 9. Two-Tone Power Gain versus Output Power

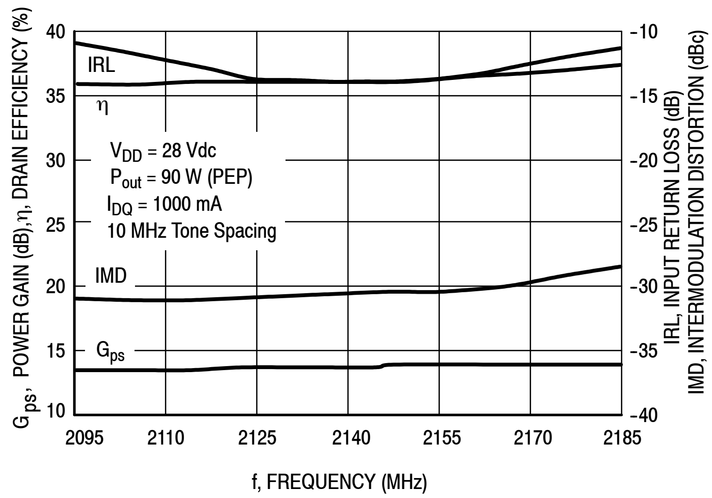


Figure 10. Two-Tone Broadband Performance

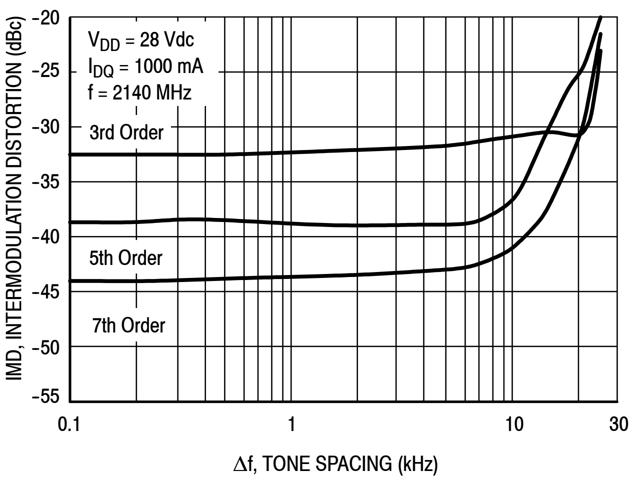


Figure 11. Intermodulation Distortion Products versus Two-Tone Spacing

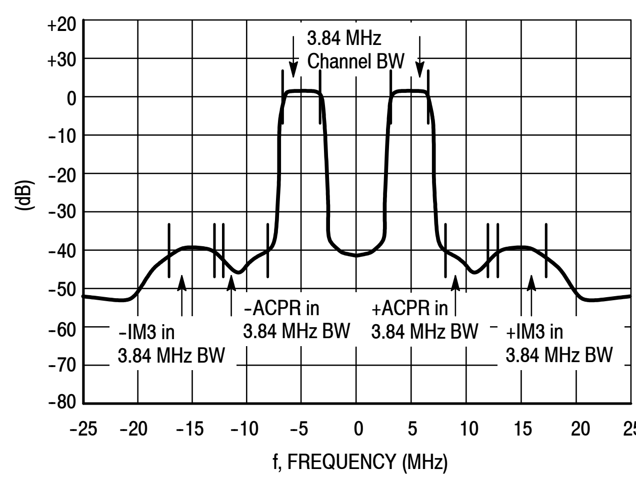
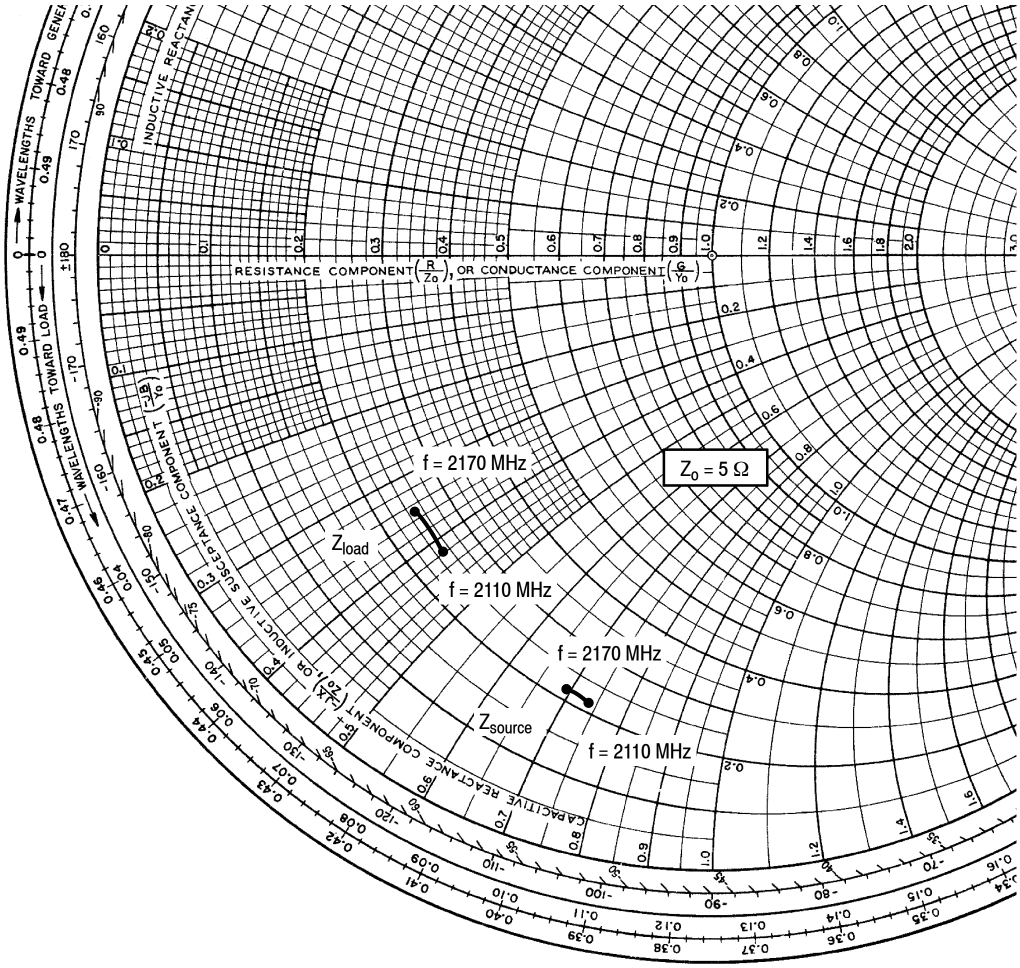


Figure 12. 2-Carrier W-CDMA Spectrum



V_{DD} = 28 V, I_{DQ} = 1000 mA, P_{out} = 19 W Avg.

f MHz	Z_{source} Ω	Z_{load} Ω
2110	1.10 - j3.71	1.23 - j2.10
2140	1.11 - j3.57	1.26 - j1.92
2170	1.12 - j3.40	1.25 - j1.76

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

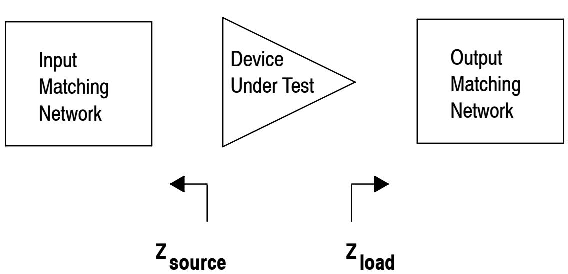
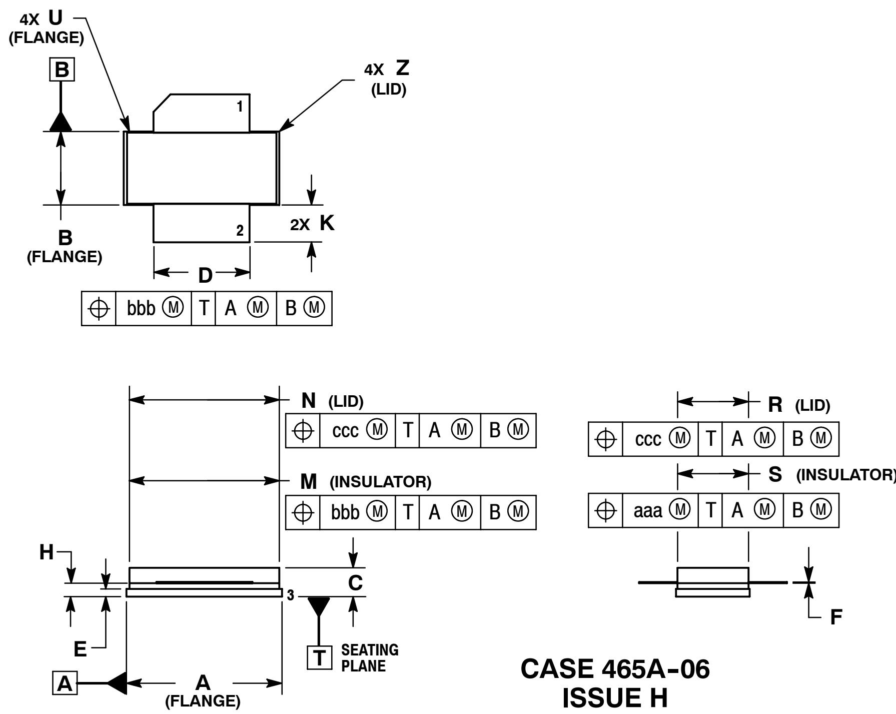


Figure 13. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
5. SOURCE

CASE 465A-06
ISSUE H
NI-780S
MRF21085LSR3

ARCHIVE INFORMATION

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
11	Oct. 2008	• Data sheet revised to reflect part status change, p. 1, including use of applicable overlay. • Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN12779, p. 1, 2 • Added Product Documentation and Revision History, p. 10 • Data sheet split due to change in part life cycle (-1, -2 added to enable visibility on web).
	Dec. 2010	• MRF21085-2 Rev. 11 (MRF21085LSR3) data sheet archived. Part no longer manufactured. See MRF21085-1 Rev. 10 for MRF21085LR3.

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Freescale Semiconductor, Inc.
Technical Information Center, EL516
2100 East Elliot Road
Tempe, Arizona 85284
1-800-521-6274 or +1-480-768-2130
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Europe, Middle East, and Africa:
Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
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+46 8 52200080 (English)
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Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor China Ltd.
Exchange Building 23F
No. 118 Jianguo Road
Chaoyang District
Beijing 100022
China
+86 10 5879 8000
support.asia@freescale.com

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